

TBB1002

Twin Built in Biasing Circuit MOS FET IC VHF/UHF RF Amplifier

REJ03G0841-0900

Rev.9.00

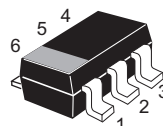
Aug 22, 2006

Features

- Small SMD package CMPAK-6 built in twin BBFET; To reduce using parts cost & PC board space.
- Suitable for World Standard Tuner RF amplifier.
- Very useful for total tuner cost reduction.
- Withstanding to ESD; Built in ESD absorbing diode. Withstand up to 200 V at C = 200 pF, Rs = 0 conditions.
- Provide mini mold packages; CMPAK-6

Outline

RENESAS Package code: PTSP0006JA-A
(Package name: CMPAK-6)



1. Gate-1(1)
2. Source
3. Drain(1)
4. Drain(2)
5. Gate-2
6. Gate-1(2)

- Notes:
1. Marking is "BM".
 2. TBB1002 is individual type number of RENESAS TWIN BBFET.

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	6	V
Gate1 to source voltage	V_{G1S}	+6 -0	V
Gate2 to source voltage	V_{G2S}	+6 -0	V
Drain current	I_D	30	mA
Channel power dissipation	P_{ch}^{*3}	250	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 3. Value on the glass epoxy board (49mm × 38mm × 1mm).

Electrical Characteristics

(Ta = 25°C)

The below specification are applicable for UHF unit (FET1)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	6	—	—	V	$I_D = 200 \mu A$, $V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+6	—	—	V	$I_{G1} = +10 \mu A$, $V_{G2S} = V_{DS} = 0$
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	+6	—	—	V	$I_{G2} = +10 \mu A$, $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff current	I_{G1SS}	—	—	+100	nA	$V_{G1S} = +5 V$, $V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	I_{G2SS}	—	—	+100	nA	$V_{G2S} = +5 V$, $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.5	0.75	1.0	V	$V_{DS} = 5 V$, $V_{G2S} = 4 V$ $I_D = 100 \mu A$
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.5	0.75	1.0	V	$V_{DS} = 5 V$, $V_{G1S} = 5 V$ $I_D = 100 \mu A$
Drain current	$I_{D(op)}$	13	17	21	mA	$V_{DS} = 5 V$, $V_{G1} = 5 V$ $V_{G2S} = 4 V$, $R_G = 100 k\Omega$
Forward transfer admittance	$ y_{fs} $	21	26	31	mS	$V_{DS} = 5 V$, $V_{G1} = 5 V$, $V_{G2S} = 4 V$ $R_G = 100 k\Omega$, $f = 1 kHz$
Input capacitance	C_{iss}	1.4	1.8	2.2	pF	$V_{DS} = 5 V$, $V_{G1} = 5 V$
Output capacitance	C_{oss}	1.0	1.4	1.8	pF	$V_{G2S} = 4 V$, $R_G = 100 k\Omega$
Reverse transfer capacitance	C_{rss}	—	0.02	0.04	pF	$f = 1 MHz$
Power gain	PG	16	21	—	dB	$V_{DS} = V_{G1} = 5 V$, $V_{G2S} = 4 V$ $R_G = 100 k\Omega$, $f = 900 MHz$
Noise figure	NF	—	1.7	2.5	dB	$Z_i = S11^*$, $Z_o = S22^* (:PG)$ $Z_i = S11opt (:NF)$

Electrical Characteristics (cont.)

(Ta = 25°C)

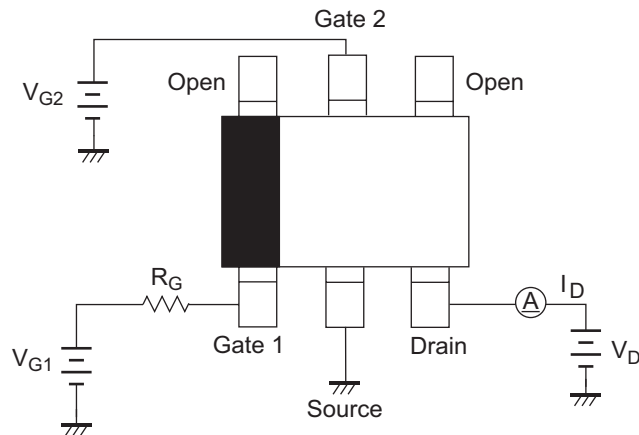
The below specification are applicable for VHF unit (FET2)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	6	—	—	V	$I_D = 200\ \mu A$, $V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+6	—	—	V	$I_{G1} = +10\ \mu A$, $V_{G2S} = V_{DS} = 0$
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	+6	—	—	V	$I_{G2} = +10\ \mu A$, $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff current	I_{G1SS}	—	—	+100	nA	$V_{G1S} = +5\ V$, $V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	I_{G2SS}	—	—	+100	nA	$V_{G2S} = +5\ V$, $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.5	0.75	1.0	V	$V_{DS} = 5\ V$, $V_{G2S} = 4\ V$ $I_D = 100\ \mu A$
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.5	0.75	1.0	V	$V_{DS} = 5\ V$, $V_{G1S} = 5\ V$ $I_D = 100\ \mu A$
Drain current	$I_{D(op)}$	14	18	22	mA	$V_{DS} = 5V$, $V_{G1} = 5\ V$, $V_{G2S} = 4\ V$ $R_G = 82\ k\Omega$
Forward transfer admittance	$ y_{fs} $	20	25	30	mS	$V_{DS} = 5\ V$, $V_{G1} = 5\ V$ $V_{G2S} = 4\ V$, $R_G = 82\ k\Omega$ $f = 1\ kHz$
Input capacitance	C_{iss}	2.2	2.6	3.0	pF	$V_{DS} = 5\ V$, $V_{G1} = 5\ V$ $V_{G2S} = 4\ V$, $R_G = 82\ k\Omega$ $f = 1\ MHz$
Output capacitance	C_{oss}	1.2	1.6	2.0	pF	
Reverse transfer capacitance	C_{rss}	—	0.03	0.05	pF	
Power gain	PG	22	27	—	dB	$V_{DS} = V_{G1} = 5\ V$, $V_{G2S} = 4\ V$ $R_G = 82\ k\Omega$, $f = 200\ MHz$
Noise figure	NF	—	1.2	1.7	dB	

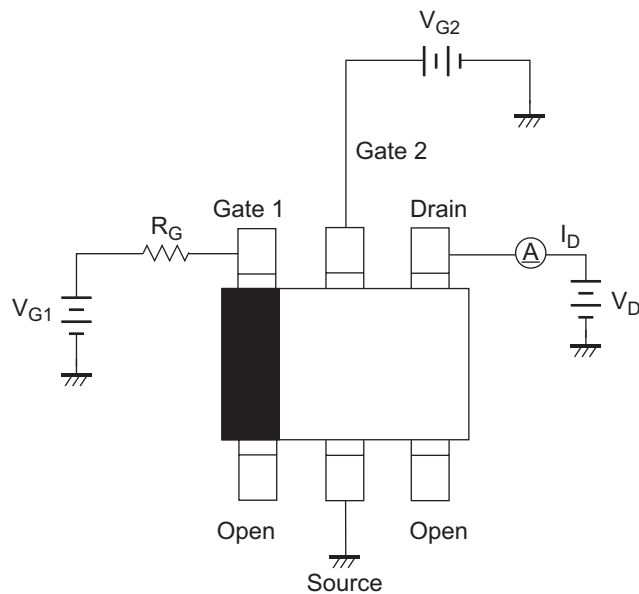
Test Circuits

- DC Biasing Circuit for Operating Characteristic Items ($I_{D(op)}$, $|y_{fs}|$, C_{iss} , C_{oss} , C_{rss} , NF , PG)

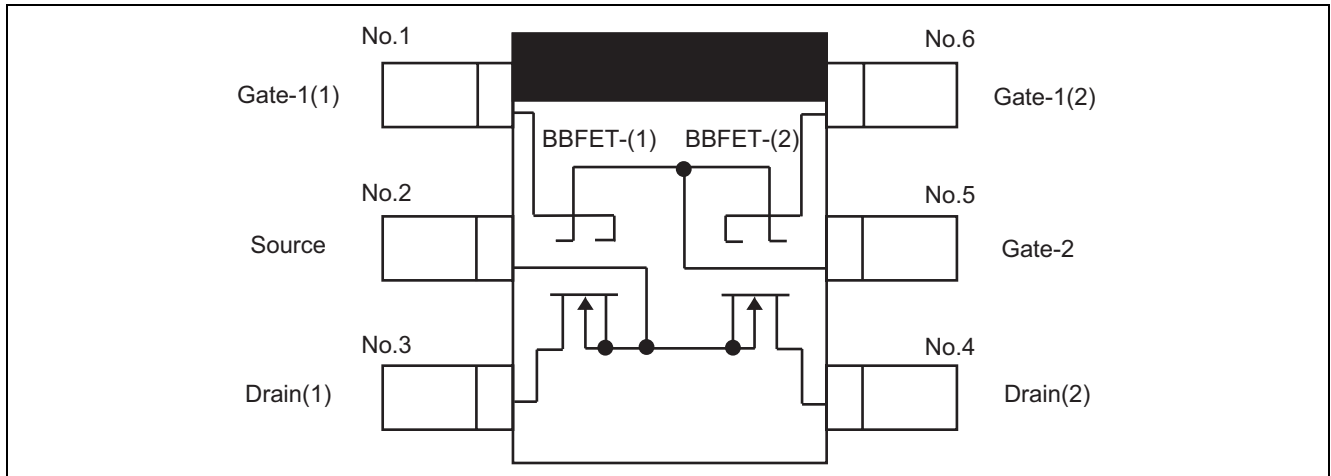
Measurement of FET1



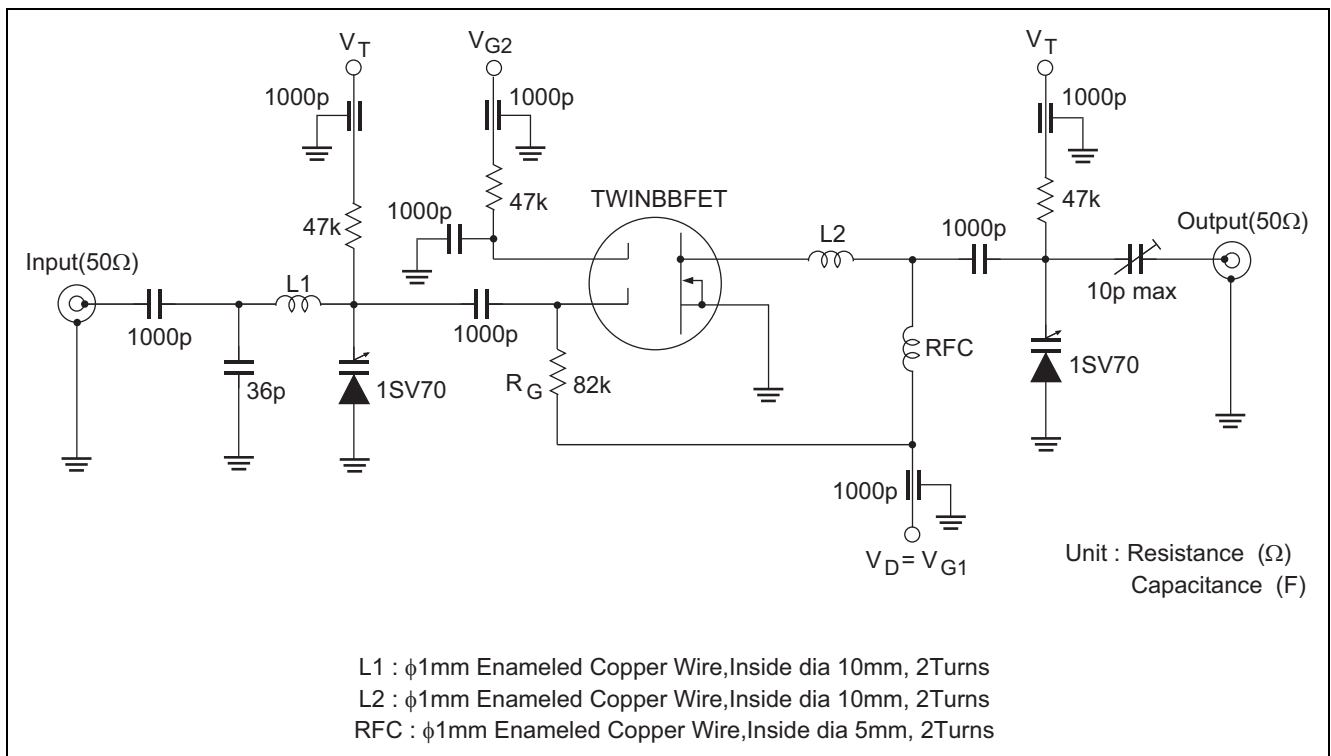
Measurement of FET2

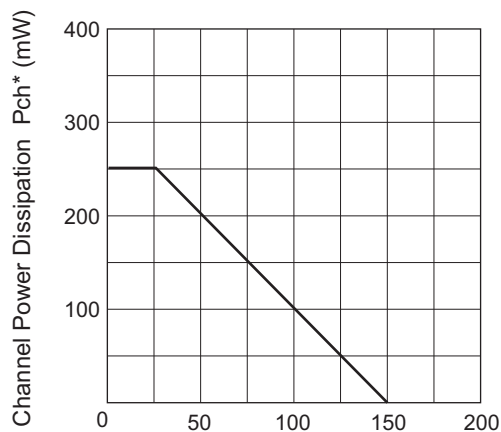


• Equivalent Circuit



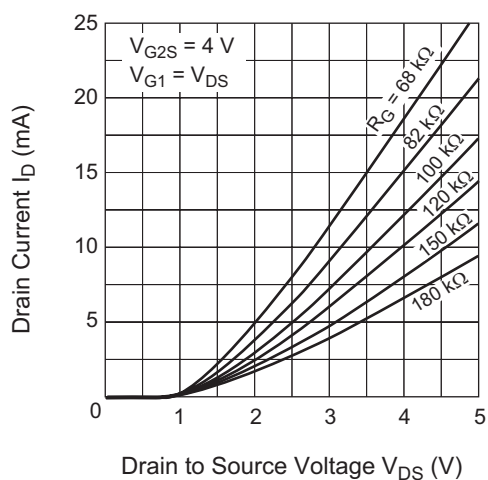
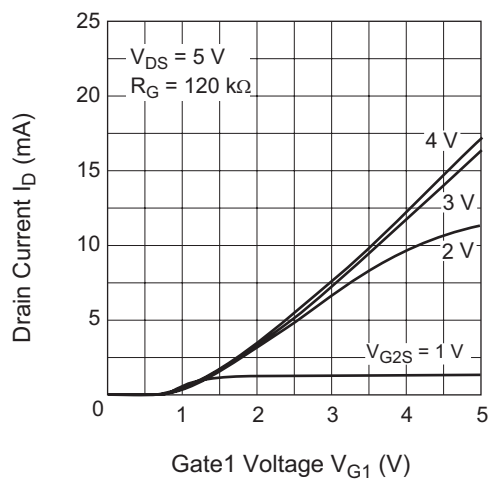
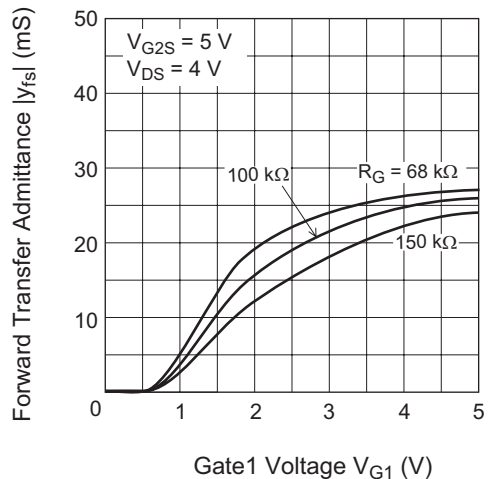
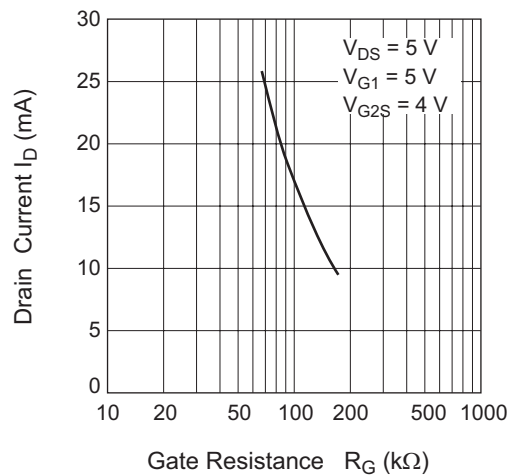
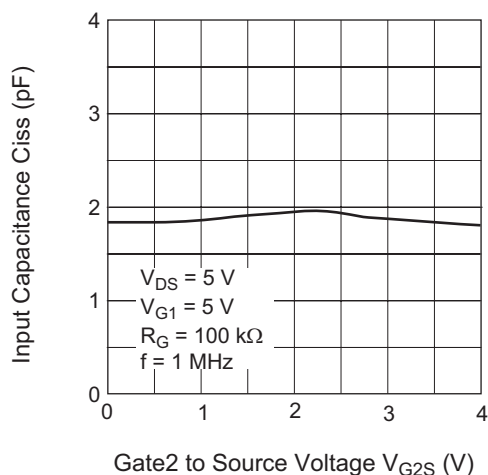
• 200 MHz Power Gain, Noise Figure Test Circuit



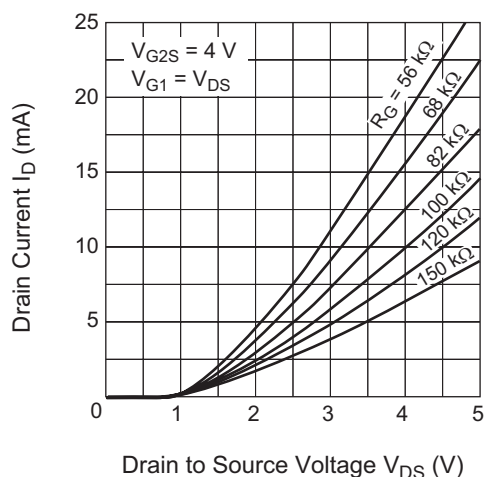
Maximum Channel Power
Dissipation CurveAmbient Temperature T_a (°C)

* Value on the glass epoxy board (49mm × 38mm × 1mm)

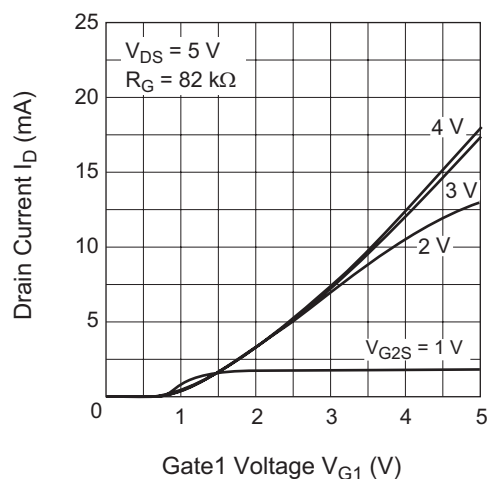
Typical Output Characteristics (FET1)

Drain Current vs.
Gate1 Voltage (FET1)Forward Transfer Admittance
vs. Gate1 Voltage (FET1)Drain Current vs.
Gate Resistance (FET1)Input Capacitance vs.
Gate2 to Source Voltage (FET1)

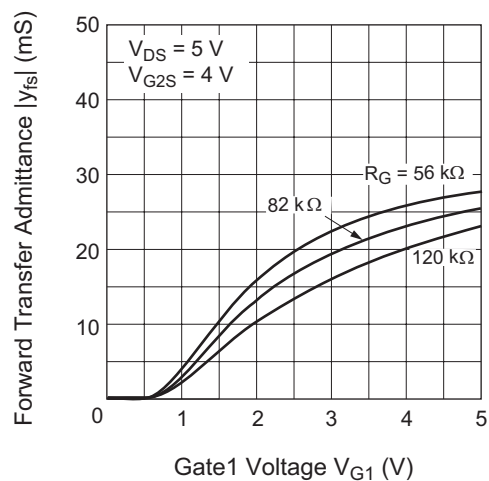
Typical Output Characteristics (FET2)



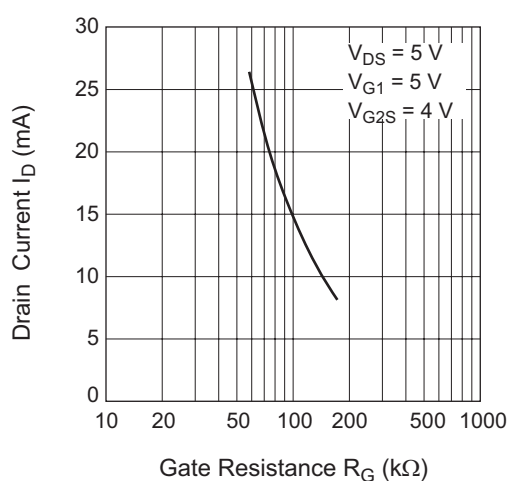
Drain Current vs. Gate1 Voltage (FET2)



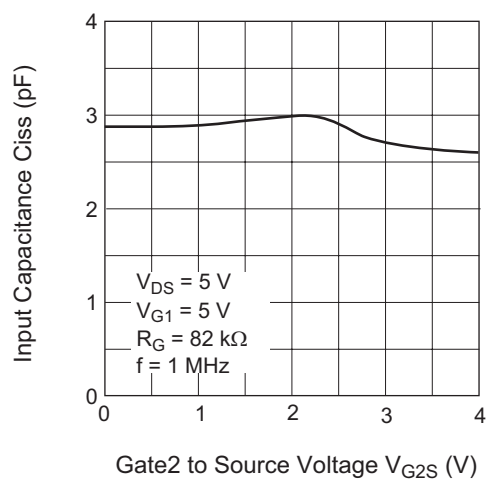
Forward Transfer Admittance vs. Gate1 Voltage (FET2)



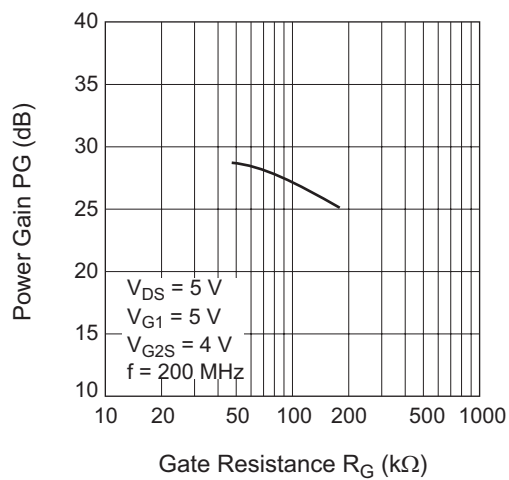
Drain Current vs. Gate Resistance (FET2)

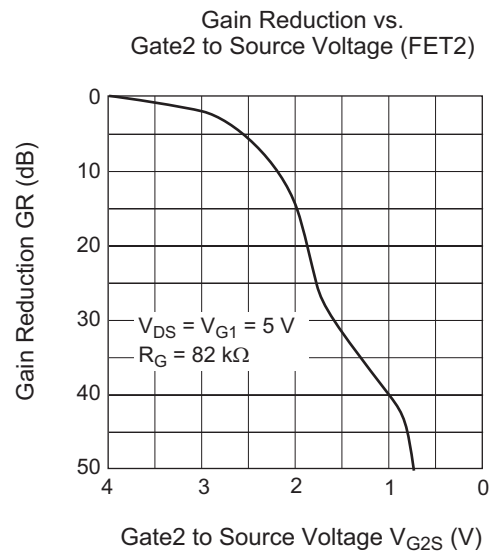
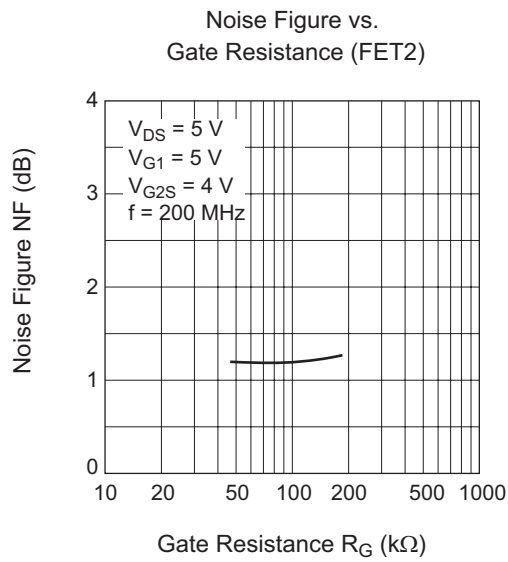


Input Capacitance vs. Gate2 to Source Voltage (FET2)

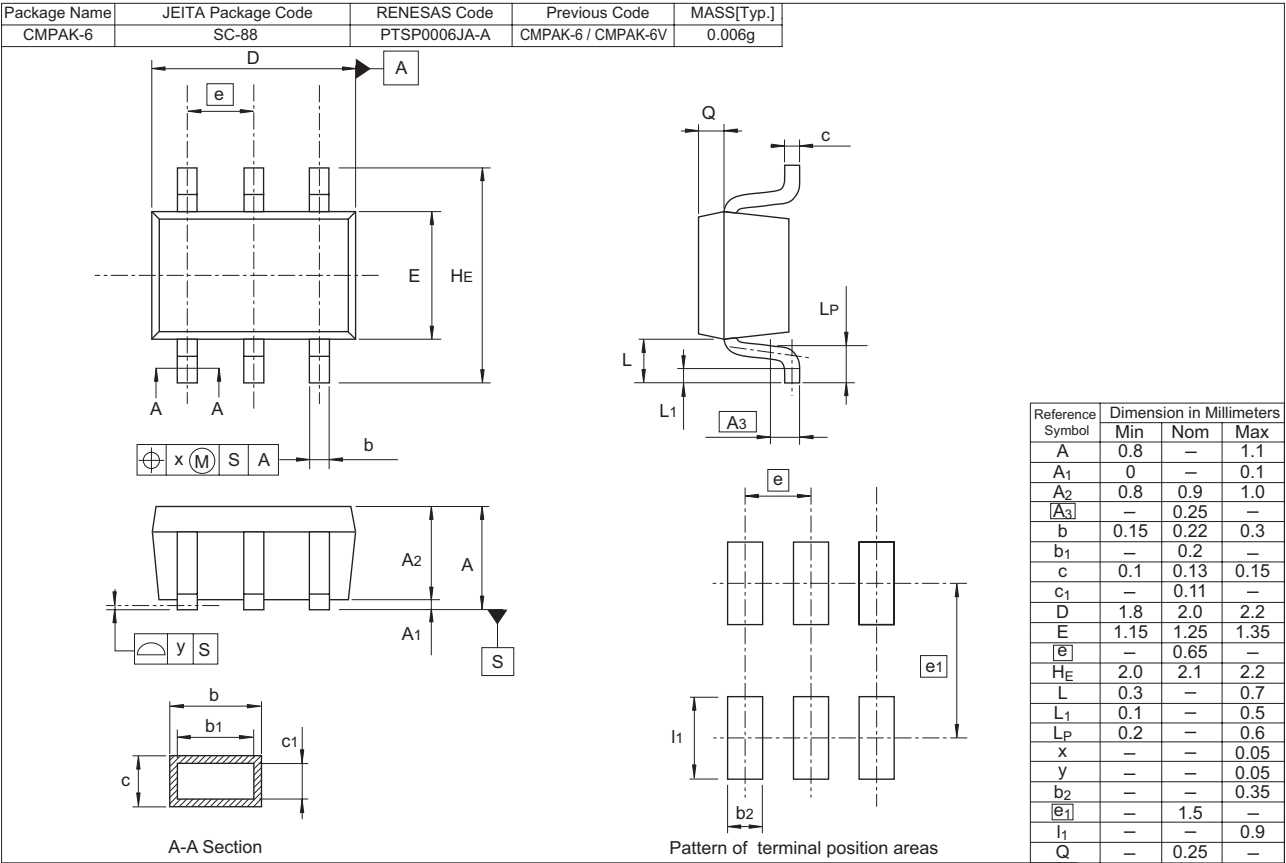


Power Gain vs. Gate Resistance (FET2)





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
TBB1002BMTL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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